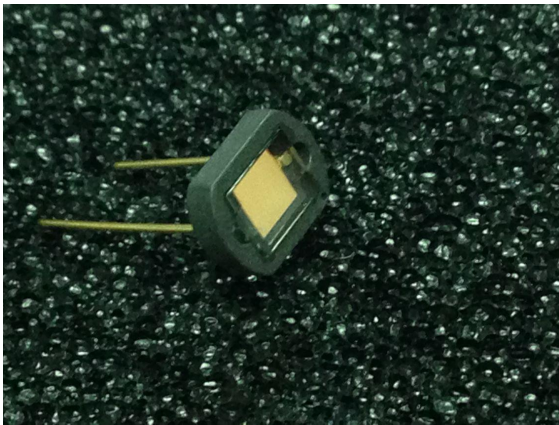


Selective wavelength photodiode

OSD9-52C



Description

The OSD9-52C is 520nm peak wave response high-output, high-speed silicon photo diode which is mounted in 2PIN ceramic package, permits wide angular response.

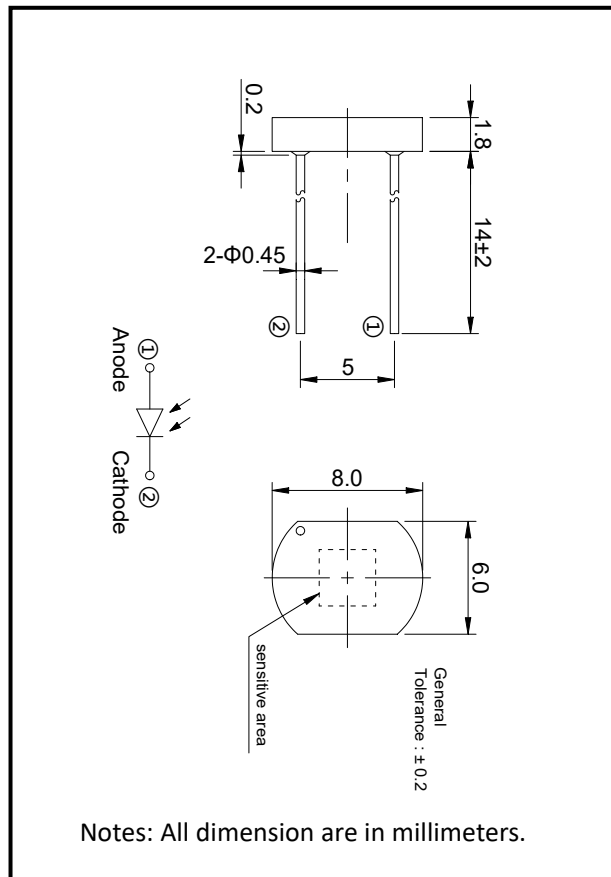
Applications

*Color sensor *Laser detect * Medical equipment

Absolute Maximum Ratings (Ta=23°C)



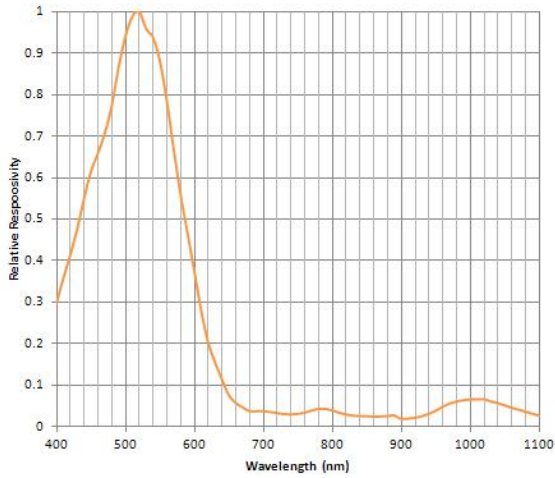
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Chip size	size	-		3.17*3.17		mm ²
Active area	A	-		2.84*2.84		mm ²
Dark current	I _D	V _R =10mV		10		pA
		V _R =10V		11		
Rise time	t _R	V _R =0V; λ =520nm; R _L =50Ω		300		ns
Tempcoeffi-cient of I _D	T _{CID}			0.18		times/°C
Reverse breakdown voltage	V _{(BR)R}	I _R =100uA E _v =0mw/cm ²	33			V
Junction Capacitance	C _J	V _R =0V f=1MHz E _e =0mW/cm ²		67		pF
		V _R =5V f=1MHz E _e =0mW/cm ²		51		
Photo sensitivity	S _R	520nm		0.45		A/W
Spectral Application Range	λ range		350		700	nm
Spectral Response-Peak	λ _p			520		nm
Shunt resistance	R _{sh}	V _R =10mV		0.1		GΩ
Angular Resp 50% Resp Pt	θ ^{1/2}			±20		Degrees



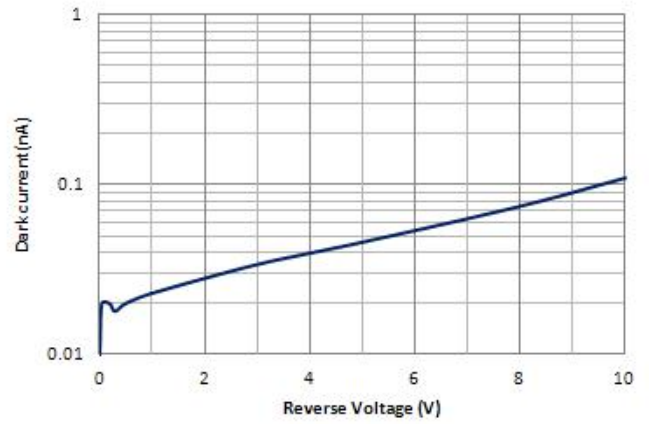


OSD9-52C

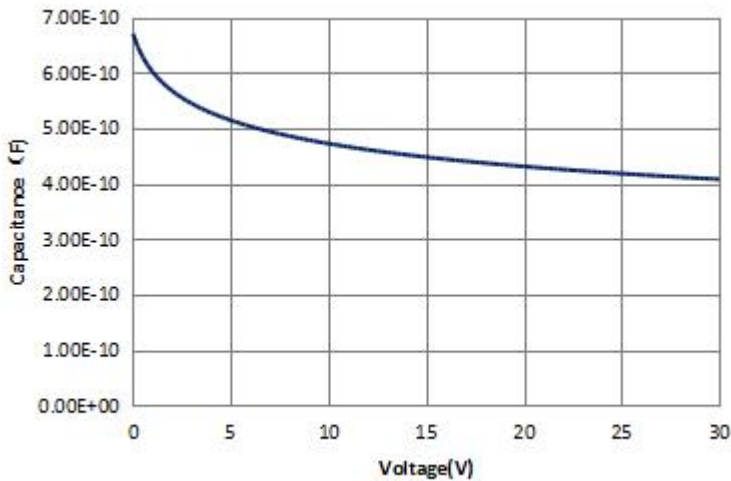
SPECTRAL RESPONSE (Ta=23°C)



DARK CURRENT VS. REVERSE VOLTAGE (Ta=23°C)



CAPACITANCE VS. REVERSE VOLTAGE (Ta=23°C)



Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice.

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